

We focus on power.

RIDGE WAVEGUIDE LASER with AR-COATING

GaAs Semiconductor Laser Diode Tunable Fabry-Perot Laser for External Cavity Operation



General Product Information

Product	Application
tunable 1120 nm Fabry-Perot Laser	Spectroscopy
for use in an External Cavity Diode Laser (ECDL)	
sealed SOT Housing	
Monitor Diode	



Absolute Maximum Ratings

	Symbol	Unit	min	typ	max
Storage Temperature	T_S	°C	-20		85
Operational Temperature at Case	T_{C}	°C	-20		50
Forward Current	I _F	mA			180
Reverse Voltage	V_R	V			0
Output Power (extracavity)	P_{opt}	mW			60

Stress in excess of the Absolute Maximum Ratings can cause permanent damage to the device.

Recommended Operational Conditions

	Symbol	Unit	min	typ	max
Operational Temperature at Case	T _C	°C	15		40
Forward Current	I _F	mA			160

Characteristics at T_{LD} = 25 °C at Begin Of Life

Parameter	Symbol	Unit	min	typ	max
Center Wavelength	λ_{C}	nm		1120	
Tuning Range	$\Delta \lambda_{\text{tun}}$	nm	1060		1130
Output Power (extracavity)	P_{opt}	mW		50	
Cavity Length	L	μm		1300	
Reflectivity at Front Facet	R_{ff}			3·10 ⁻⁴	1·10 ⁻³
Polarization				TE	
Spatial Mode (transversal) TEM ₀₀					
Spectral Mode (longitudinal)			Sin	gle/Multi Mo	ode

Measurement Conditions / Comments

Tuning range and output power are estimated from the gain profile of the laser. The actual achieved wavelength and power are strongly influenced by the external cavity. Therefore eagleyard Photonics will give no guarantee on these parameters.

E field parallel to Pin 2 - Pin 3 - plane
Fundamental Mode
depending on operating conditions





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Monitor Diode					
Parameter	Symbol	Unit	min	typ	max
Monitor Detector Responsivity	I _{mon} / P _{opt}	μA / mW	2		40
Reverse Voltage Monitor Diode	U_RMD	V	3		5

Measurement Conditions / Comments	
$U_R = 5 \text{ V}$; P_{opt} intracavity	

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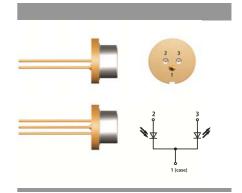
Package Dimensions

Parameter	Symbol	Unit	min	typ	max
Height of Emission Plane	d _{EP}	mm	3.50	3.65	3.70
Excentricity of Emission Center	R	mm			0.12
Pin Length	I _{PIN}	mm		14	

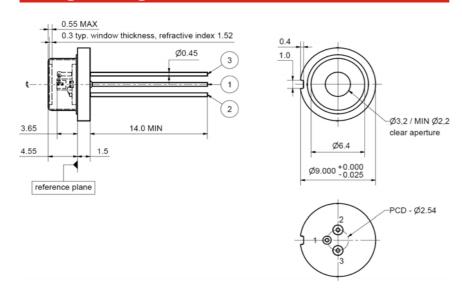
Measurement Conditions / Comments			
reference plane: top side of TO header			
reference: center of outer diameter of header			

Package Pinout

Ground	1
Photo Diode (+)	2
Laser (+)	3



Package Drawings



Z11-SPEC-SOT02-COM-000





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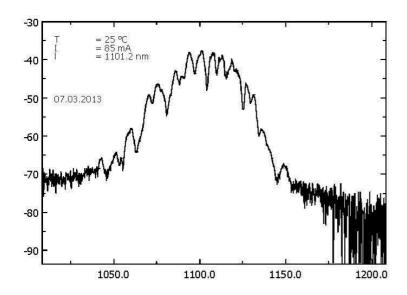
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Typical Measurement Results

Emission Spectrum measured without external feedback



Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.

Ordering Information:



800 Village Walk #316 Guilford, CT 06437 Ph: 203-401-8093

Email orders to: sales@xsoptix.com Fax orders to: 800-878-7282

Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.

The RWE diode type is known to be sensitive against thermal stress. It should not be operated without appropriate optical feedback from an external cavity. Operating at moderate temperatures on proper heat sinks will contribute to a long lifetime of the diode.

The laser emission from this diode is close to the invisible infrared region of the electromagnetic spectrum. Avoid direct and/or indirect exposure to the free running beam. Collimating the free running beam with optics as common in optical instruments will increase threat to the human eye.

Each laser diode will come with an individual test protocol verifying the parameters given in this document.











